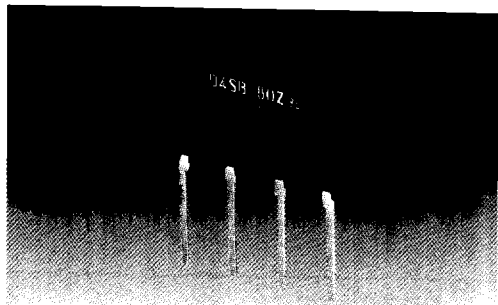
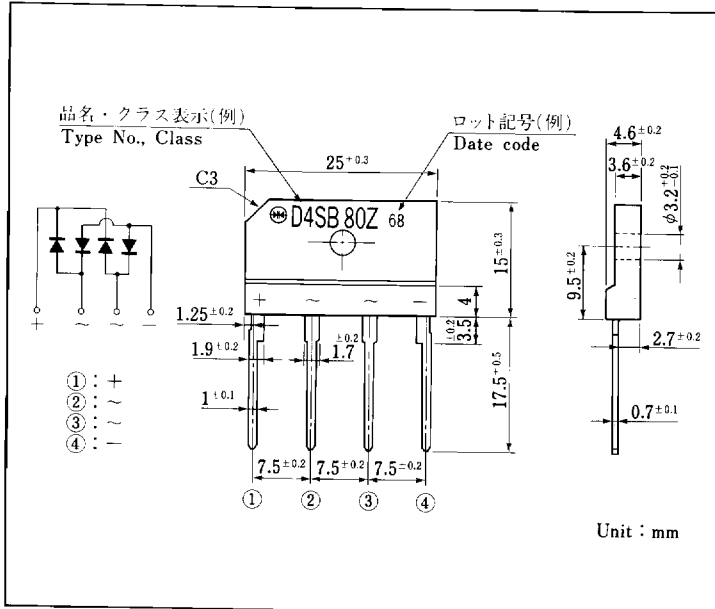


D4SB□Z

800V 4A



■ 外形寸法図 OUTLINE DIMENSIONS



■ 定格表 RATINGS

絶対最大定格 Absolute Maximum Ratings

項目 Item	記号 Symbol	条件 Conditions	品名 Type No.	D4SB80Z	単位 Unit
保存温度 Storage Temperature	Tstg			-40~150	°C
接合部温度 Operating Junction Temperature	Tj			150	°C
せん頭逆電圧 Mainum Reverse Voltage	VRM			800	V
出力電流 Average Rectified Forward Current	Io	50Hz正弦波, 抵抗負荷 50Hz sine wave, R-load	フィン付き With heatsink Tc=108°C フィンなし Without heatsink Ta=25°C	4 2.3	A
せん頭サージ順電流 Peak Surge Forward Current	IFSM	50Hz正弦波, 非繰り返し1サイクルせん頭値, Tj=25°C 50Hz sine wave, Non-repetitive 1 cycle peak value, Tj=25°C		150	A
電流2乗時間積 Current Squared Time	I <sup>2</sup> t	1ms ≤ t < 10ms Tc=25°C		80	A <sup>2</sup> s
せん頭サージ逆電力 Peak Surge Reverse Power	PRSM	パルス幅10μs, 非繰り返し, 1素子当り, Tj=25°C Pulse width 10μs, Non-repetitive, Rating of per diode, Tj=25°C		5	kW
絶縁耐圧 Dielectric Strength	Vdis	一括端子・ケース間, AC 1分間印加 Terminals to case, AC 1 minute		2	kV
締め付けトルク Mounting Torque	TOR	(推奨値: 5kg·cm) (Recommended torque: 5kg·cm)		8	kg·cm

電氣的・熱的特性 Electrical Characteristics (Tc=25°C)

順電圧 Forward Voltage	VF	IF=2A, パルス測定, 1素子当りの規格値 Pulse measurement, Rating of per diode	MAX 1.05	V
逆電流 Reverse Current	IR	VR=VRM, パルス測定, 1素子当りの規格値 Pulse measurement, Rating of per diode	MAX 10	μA
降伏電圧 Avalanche Voltage	VZ	IR=1mA, 1素子当りの規格値 Rating of per diode	MIN 1000	V
熱抵抗 Thermal Resistance	θjc	接合部・ケース間, フィン付き Between junction and case, With heatsink	MAX 5.5	°C/W
	θjl	接合部・リード間, フィンなし Between junction and lead, Without heatsink	MAX 6	
	θja	接合部・周囲間, フィンなし Between junction and ambient, Without heatsink	MAX 30	

■ 特性図 CHARACTERISTIC DIAGRAMS

